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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	444
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	676-BGA
Supplier Device Package	676-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe1500-2fg676

Advanced Architecture

The proprietary ProASIC3E architecture provides granularity comparable to standard-cell ASICs. The ProASIC3E device consists of five distinct and programmable architectural features (Figure 1-1 on page 3):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory
- Extensive CCCs and PLLs
- Pro I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the ProASIC3E core tile as either a three-input lookup table (LUT) equivalent or as a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the ProASIC family of third-generation architecture Flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

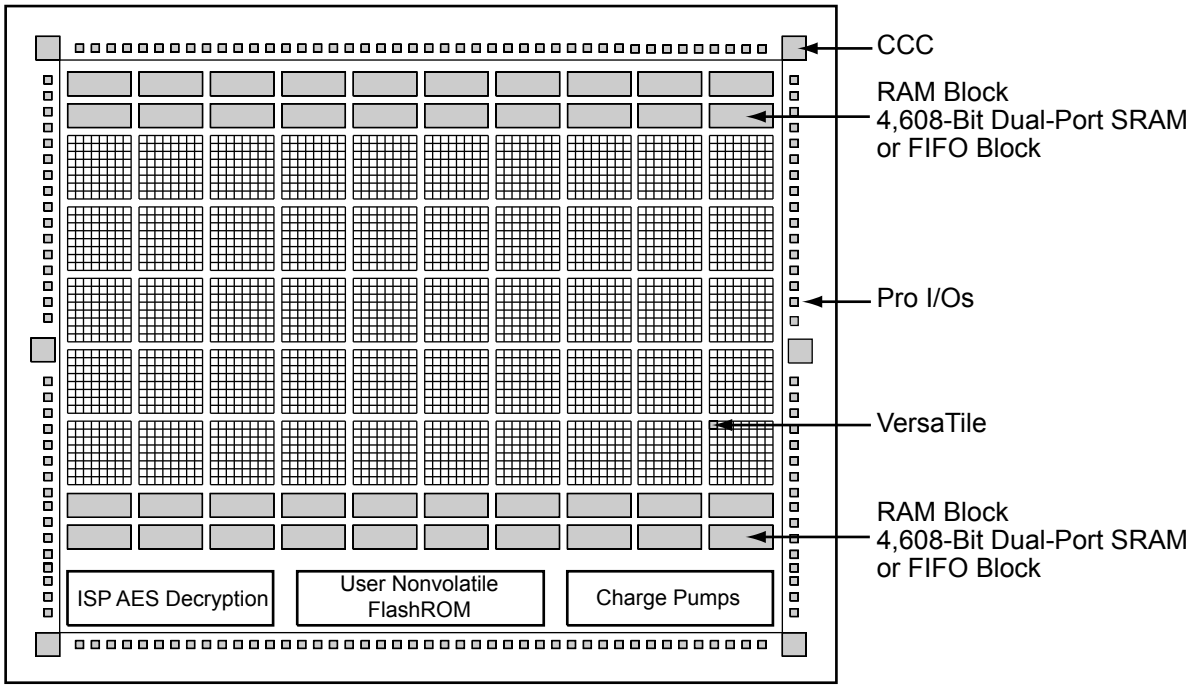


Figure 1-1 • **ProASIC3E Device Architecture Overview**

SRAM and FIFO

ProASIC3E devices have embedded SRAM blocks along their north and south sides. Each variable-aspect-ratio SRAM block is 4,608 bits in size. Available memory configurations are 256×18, 512×9, 1k×4, 2k×2, and 4k×1 bits. The individual blocks have independent read and write ports that can be configured with different bit widths on each port. For example, data can be sent through a 4-bit port and read as a single bitstream. The embedded SRAM blocks can be initialized via the device JTAG port (ROM emulation mode) using the UJTAG macro.

In addition, every SRAM block has an embedded FIFO control unit. The control unit allows the SRAM block to be configured as a synchronous FIFO without using additional core VersaTiles. The FIFO width and depth are programmable. The FIFO also features programmable Almost Empty (AEMPTY) and Almost Full (AFULL) flags in addition to the normal Empty and Full flags. The embedded FIFO control unit contains the counters necessary for generation of the read and write address pointers. The embedded SRAM/FIFO blocks can be cascaded to create larger configurations.

PLL and CCC

ProASIC3E devices provide designers with very flexible clock conditioning capabilities. Each member of the ProASIC3E family contains six CCCs, each with an integrated PLL.

The six CCC blocks are located at the four corners and the centers of the east and west sides.

To maximize user I/Os, only the center east and west PLLs are available in devices using the PQ208 package. However, all six CCC blocks are still usable; the four corner CCCs allow simple clock delay operations as well as clock spine access.

The inputs of the six CCC blocks are accessible from the FPGA core or from one of several inputs located near the CCC that have dedicated connections to the CCC block.

The CCC block has these key features:

- Wide input frequency range (f_{IN_CCC}) = 1.5 MHz to 350 MHz
- Output frequency range (f_{OUT_CCC}) = 0.75 MHz to 350 MHz
- Clock delay adjustment via programmable and fixed delays from –7.56 ns to +11.12 ns
- 2 programmable delay types for clock skew minimization
- Clock frequency synthesis

Additional CCC specifications:

- Internal phase shift = 0°, 90°, 180°, and 270°. Output phase shift depends on the output divider configuration.
- Output duty cycle = 50% ± 1.5% or better
- Low output jitter: worst case < 2.5% × clock period peak-to-peak period jitter when single global network used
- Maximum acquisition time = 300 µs
- Low power consumption of 5 mW
- Exceptional tolerance to input period jitter— allowable input jitter is up to 1.5 ns
- Four precise phases; maximum misalignment between adjacent phases of 40 ps × (350 MHz / f_{OUT_CCC})

Global Clocking

ProASIC3E devices have extensive support for multiple clocking domains. In addition to the CCC and PLL support described above, there is a comprehensive global clock distribution network.

Each VersaTile input and output port has access to nine VersaNets: six chip (main) and three quadrant global networks. The VersaNets can be driven by the CCC or directly accessed from the core via multiplexers (MUXes). The VersaNets can be used to distribute low-skew clock signals or for rapid distribution of high fanout nets.

Table 2-4 • Overshoot and Undershoot Limits [1]

VCCI and VMV	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle[2]	Maximum Overshoot/ Undershoot[2]
2.7 V or less	10%	1.4 V
	5%	1.49 V
3 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

1. *Based on reliability requirements at 85°C.*
2. *The duration is allowed at one out of six clock cycles. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.*
3. *This table does not provide PCI overshoot/undershoot limits.*

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every ProASIC®3E device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges. In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in Figure 2-1 on page 2-4.

There are five regions to consider during power-up.

ProASIC3E I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points (Figure 2-1 on page 2-4).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI Trip Point:
Ramping up: 0.6 V < trip_point_up < 1.2 V
Ramping down: 0.5 V < trip_point_down < 1.1 V

VCC Trip Point:
Ramping up: 0.6 V < trip_point_up < 1.1 V
Ramping down: 0.5 V < trip_point_down < 1 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

Thermal Characteristics

Introduction

The temperature variable in Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because dynamic and static power consumption cause the chip junction to be higher than the ambient temperature.

EQ 1 can be used to calculate junction temperature.

T_J = Junction Temperature = $\Delta T + T_A$

EQ 1

where:

T_A = Ambient Temperature

ΔT = Temperature gradient between junction (silicon) and ambient $\Delta T = \theta_{ja} * P$

θ_{ja} = Junction-to-ambient of the package. θ_{ja} numbers are located in Table 2-5.

P = Power dissipation

Package Thermal Characteristics

The device junction-to-case thermal resistivity is θ_{jc} and the junction-to-ambient air thermal resistivity is θ_{ja}. The thermal characteristics for θ_{ja} are shown for two air flow rates. The absolute maximum junction temperature is 110°C. EQ 2 shows a sample calculation of the absolute maximum power dissipation allowed for an 896-pin FBGA package at commercial temperature and in still air.

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. } (°C) - \text{Max. ambient temp. } (°C)}{\theta_{ja}(°C/W)} = \frac{110°C - 70°C}{13.6°C/W} = 5.88\ W$$

EQ 2

Table 2-5 • **Package Thermal Resistivities**

Package Type	Pin Count	θ_{jc}	θ_{ja}			Units
			Still Air	200 ft./min.	500 ft./min.	
Plastic Quad Flat Package (PQFP)	208	8.0	26.1	22.5	20.8	C/W
Plastic Quad Flat Package (PQFP) with embedded heat spreader in A3PE3000	208	3.8	16.2	13.3	11.9	C/W
Fine Pitch Ball Grid Array (FBGA)	256	3.8	26.9	22.8	21.5	C/W
	484	3.2	20.5	17.0	15.9	C/W
	676	3.2	16.4	13.0	12.0	C/W
	896	2.4	13.6	10.4	9.4	C/W

Temperature and Voltage Derating Factors

Table 2-6 • **Temperature and Voltage Derating Factors for Timing Delays (normalized to T_J = 70°C, VCC = 1.425 V)**

Array Voltage VCC (V)	Junction Temperature (°C)					
	–40°C	0°C	25°C	70°C	85°C	100°C
1.425	0.87	0.92	0.95	1.00	1.02	1.04
1.500	0.83	0.88	0.90	0.95	0.97	0.98
1.575	0.80	0.85	0.87	0.92	0.93	0.95

3.3 V LVCMOS Wide Range

Table 2-29 • Minimum and Maximum DC Input and Output Levels

3.3 V LVCMOS Wide Range	Equivalent Software Default Drive Strength Option[1]	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
Drive Strength		Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	µA	µA	Max. mA[4]	Max. mA[4]	µA[5]	µA[5]
100 µA	2 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	27	25	10	10
100 µA	4 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	27	25	10	10
100 µA	6 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	54	51	10	10
100 µA	8 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	54	51	10	10
100 µA	12 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	109	103	10	10
100 µA	16 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	127	132	10	10
100 µA	24 mA	–0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	181	268	10	10

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN< VCCI. Input current is larger when operating outside recommended ranges.*
4. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
5. *Currents are measured at 85°C junction temperature.*
6. *Software default selection highlighted in gray.*

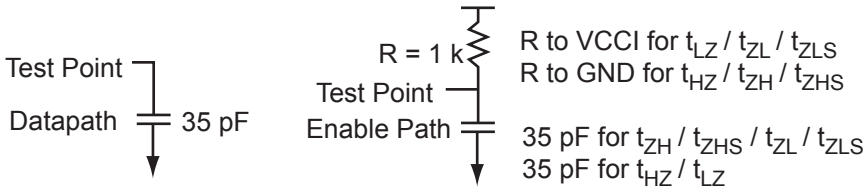


Figure 2-7 • AC Loading

Table 2-30 • 3.3 V LVCMOS Wide Range AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C_{LOAD} (pF)
0	3.3	1.4	–	35

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

3.3 V PCI, 3.3 V PCI-X

Peripheral Component Interface for 3.3 V standard specifies support for 33 MHz and 66 MHz PCI Bus applications.

Table 2-45 • Minimum and Maximum DC Input and Output Levels

3.3 V PCI/PCI-X	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
Per PCI specification	Per PCI curves										10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V< VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN< VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*

AC loadings are defined per the PCI/PCI-X specifications for the datapath; Microsemi loadings for enable path characterization are described in Figure 2-11.

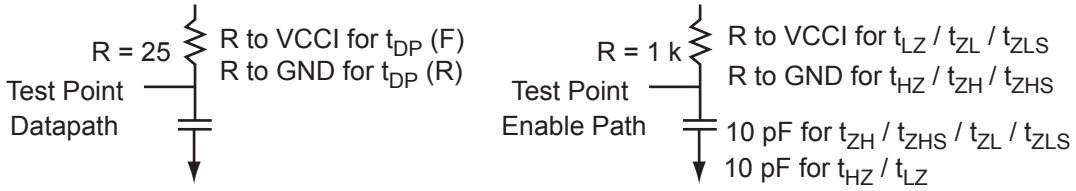


Figure 2-11 • AC Loading

AC loadings are defined per PCI/PCI-X specifications for the datapath; Microsemi loading for tristate is described in Table 2-46.

Table 2-46 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C_{LOAD} (pF)
0	3.3	0.285 * VCCI for $t_{DP(R)}$ 0.615 * VCCI for $t_{DP(F)}$	–	10

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-47 • 3.3 V PCI/PCI-X
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.66	2.81	0.04	1.05	1.67	0.43	2.86	2.00	3.28	3.61	5.09	4.23	ns
–1	0.56	2.39	0.04	0.89	1.42	0.36	2.43	1.70	2.79	3.07	4.33	3.60	ns
–2	0.49	2.09	0.03	0.78	1.25	0.32	2.13	1.49	2.45	2.70	3.80	3.16	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

2.5 V GTL

Gunning Transceiver Logic is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 2.5 V.

Table 2-51 • Minimum and Maximum DC Input and Output Levels

2.5 GTL	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min., V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
20 mA[3]	–0.3	VREF – 0.05	VREF + 0.05	3.6	0.4	–	20	20	124	169	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*
3. *Output drive strength is below JEDEC specification.*

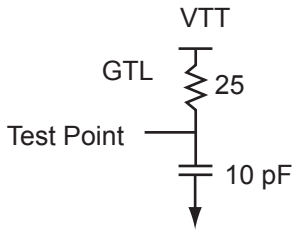


Figure 2-13 • AC Loading

Table 2-52 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.05	VREF + 0.05	0.8	0.8	1.2	10

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-53 • 2.5 V GTL
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V VREF = 0.8 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.60	2.13	0.04	2.46	0.43	2.16	2.13			4.40	4.36	ns
–1	0.51	1.81	0.04	2.09	0.36	1.84	1.81			3.74	3.71	ns
–2	0.45	1.59	0.03	1.83	0.32	1.61	1.59			3.28	3.26	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

HSTL Class II

High-Speed Transceiver Logic is a general-purpose high-speed 1.5 V bus standard (EIA/JESD8-6). ProASIC3E devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-63 • Minimum and Maximum DC Input and Output Levels

HSTL Class II	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max., V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
15 mA[3]	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	15	15	55	66	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*
3. *Output drive strength is below JEDEC specification.*

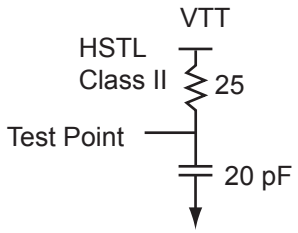


Figure 2-17 • AC Loading

Table 2-64 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.1	VREF + 0.1	0.75	0.75	0.75	20

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-65 • HSTL Class II
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V, VREF = 0.75 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.66	3.02	0.04	2.12	0.43	3.08	2.71			5.32	4.95	ns
–1	0.56	2.57	0.04	1.81	0.36	2.62	2.31			4.52	4.21	ns
–2	0.49	2.26	0.03	1.59	0.32	2.30	2.03			3.97	3.70	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Differential I/O Characteristics

Physical Implementation

Configuration of the I/O modules as a differential pair is handled by the Designer software when the user instantiates a differential I/O macro in the design.

Differential I/Os can also be used in conjunction with the embedded Input Register (InReg), Output Register (OutReg), Enable Register (EnReg), and DDR. However, there is no support for bidirectional I/Os or tristates with the LVPECL standards.

LVDS

Low-Voltage Differential Signaling (ANSI/TIA/EIA-644) is a high-speed, differential I/O standard. It requires that one data bit be carried through two signal lines, so two pins are needed. It also requires external resistor termination.

The full implementation of the LVDS transmitter and receiver is shown in an example in Figure 2-22. The building blocks of the LVDS transmitter-receiver are one transmitter macro, one receiver macro, three board resistors at the transmitter end, and one resistor at the receiver end. The values for the three driver resistors are different from those used in the LVPECL implementation because the output standard specifications are different.

Along with LVDS I/O, ProASIC3E also supports Bus LVDS structure and Multipoint LVDS (M-LVDS) configuration (up to 40 nodes).

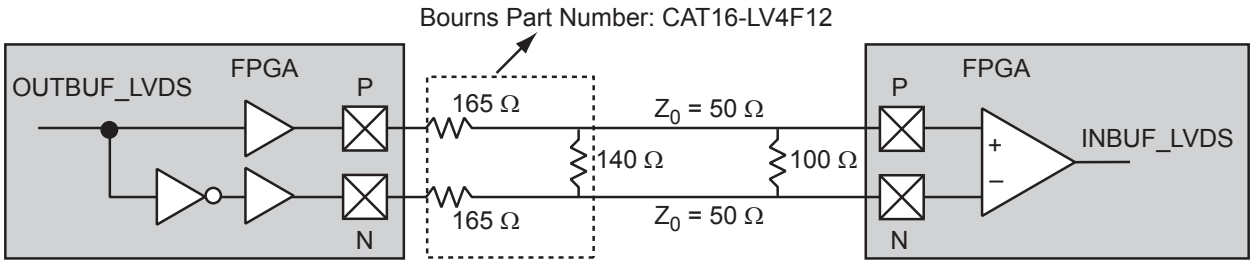


Figure 2-22 • **LVDS Circuit Diagram and Board-Level Implementation**

Input Register

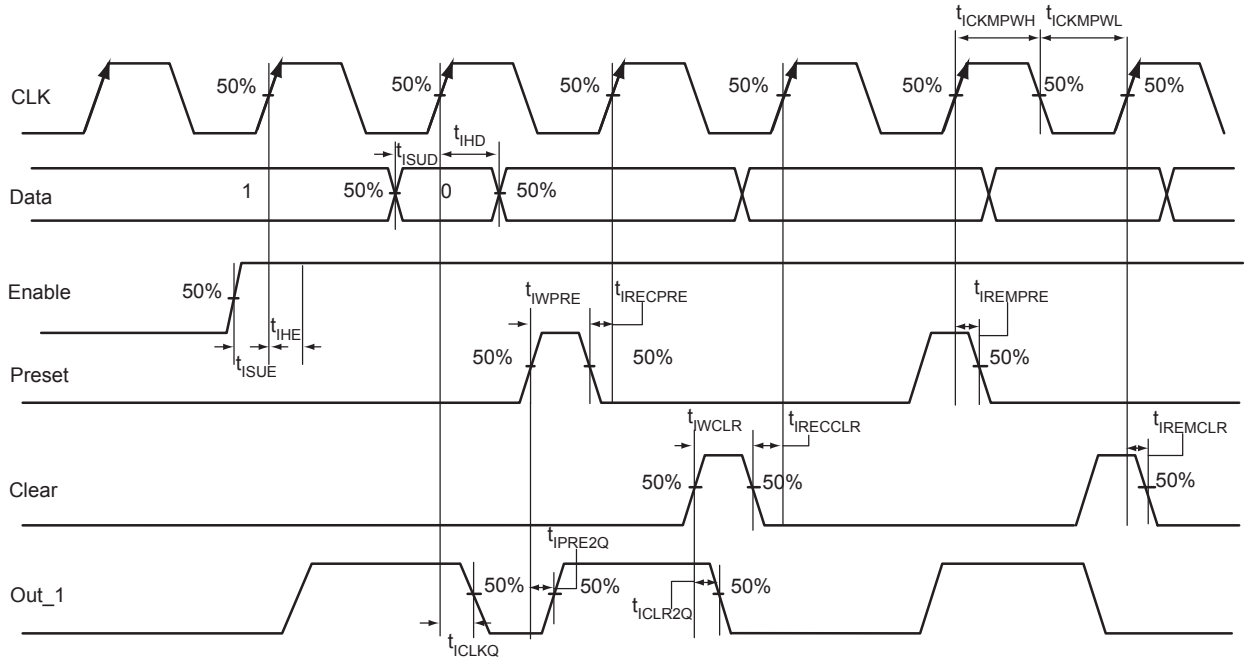


Figure 2-27 • **Input Register Timing Diagram**

Timing Characteristics

Table 2-86 • **Input Data Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.24	0.27	0.32	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.26	0.30	0.35	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	0.00	0.00	ns
t_{ISUE}	Enable Setup Time for the Input Data Register	0.37	0.42	0.50	ns
t_{IHE}	Enable Hold Time for the Input Data Register	0.00	0.00	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.45	0.52	0.61	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.45	0.52	0.61	ns
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	0.00	0.00	0.00	ns
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	0.22	0.25	0.30	ns
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	0.00	0.00	0.00	ns
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	0.22	0.25	0.30	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.22	0.25	0.30	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.22	0.25	0.30	ns
$t_{ICKMPWH}$	Clock Minimum Pulse Width High for the Input Data Register	0.36	0.41	0.48	ns
$t_{ICKMPWL}$	Clock Minimum Pulse Width Low for the Input Data Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Output Enable Register

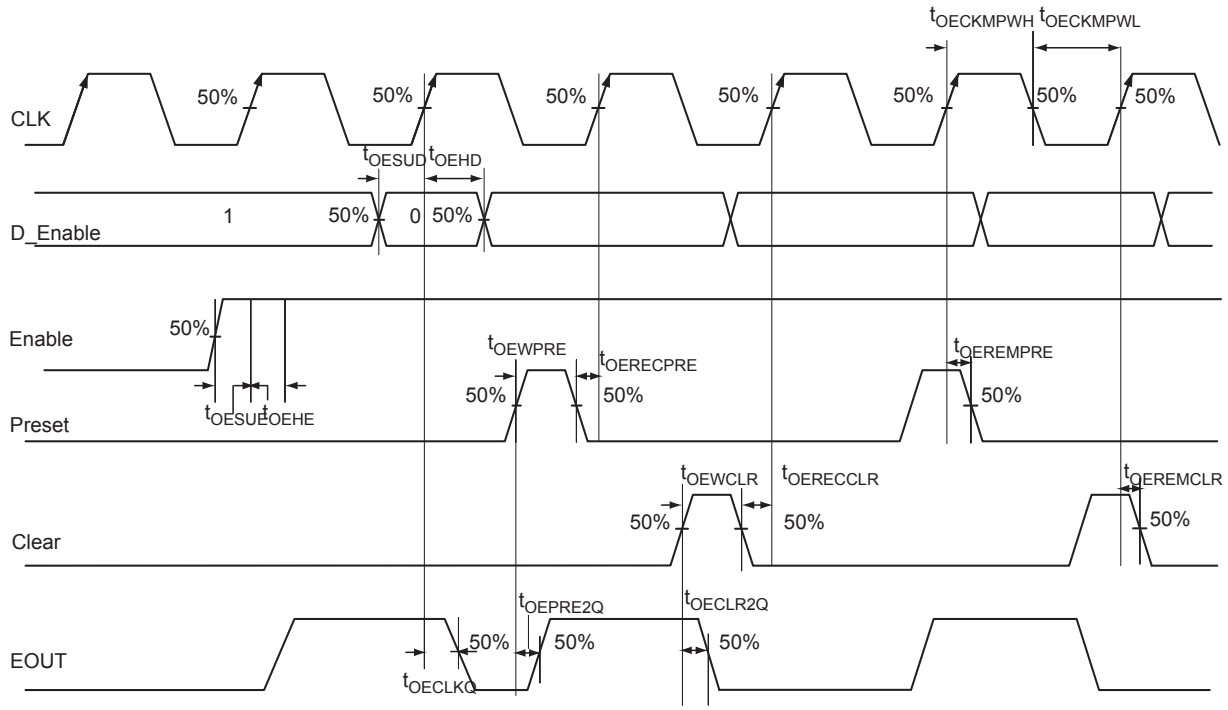


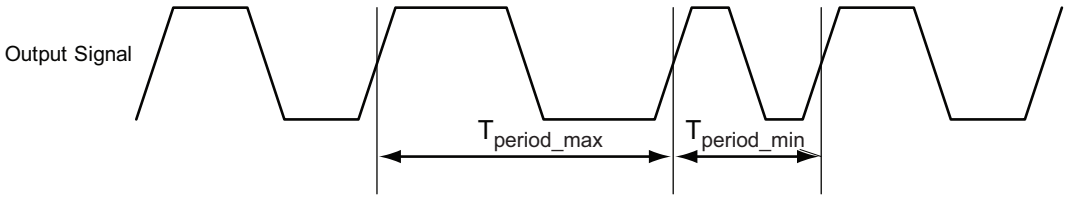
Figure 2-29 • **Output Enable Register Timing Diagram**

Timing Characteristics

Table 2-88 • **Output Enable Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.59	0.67	0.79	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.31	0.36	0.42	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	0.00	0.00	ns
t_{OESUE}	Enable Setup Time for the Output Enable Register	0.44	0.50	0.58	ns
t_{OEHE}	Enable Hold Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	0.67	0.76	0.89	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	0.67	0.76	0.89	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.22	0.25	0.30	ns
t_{OEWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.22	0.25	0.30	ns
t_{OEWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.36	0.41	0.48	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.



Note: Peak-to-peak jitter measurements are defined by $T_{peak\text{-}to\text{-}peak} = T_{period\_max} - T_{period\_min}$.

Figure 2-39 • **Peak-to-Peak Jitter Definition**

Timing Characteristics

Table 2-101 • FIFO
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{ENS}	REN, WEN Setup Time	1.38	1.57	1.84	ns
t_{ENH}	REN, WEN Hold Time	0.02	0.02	0.02	ns
t_{BKS}	BLK Setup Time	0.19	0.22	0.26	ns
t_{BKH}	BLK Hold Time	0.00	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (pass-through)	2.36	2.68	3.15	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	0.89	1.02	1.20	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
t_{WCKFF}	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (pass-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET Removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET Recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
t_{CYC}	Clock Cycle Time	3.23	3.68	4.32	ns
F_{MAX}	Maximum Frequency	310	272	231	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Refer to the I/O Structure section of the *ProASIC3E FPGA Fabric User's Guide* for an explanation of the naming of global pins.

JTAG Pins

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the part must be supplied to allow JTAG signals to transition the device. Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

TCK Test Clock

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pull-up/-down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500 W to 1 kΩ will satisfy the requirements. Refer to Table 3-1 for more information.

***Table 3-1* • Recommended Tie-Off Values for the TCK and TRST Pins**

VJTAG	Tie-Off Resistance
VJTAG at 3.3 V	200 Ω to 1 kΩ
VJTAG at 2.5 V	200 Ω to 1 kΩ
VJTAG at 1.8 V	500 Ω to 1 kΩ
VJTAG at 1.5 V	500 Ω to 1 kΩ

Notes:

1. *Equivalent parallel resistance if more than one device is on the JTAG chain*
2. *The TCK pin can be pulled up/down.*
3. *The TRST pin is pulled down.*

TDI Test Data Input

Serial input for JTAG boundary scan, ISP, and UJTAG usage. There is an internal weak pull-up resistor on the TDI pin.

TDO Test Data Output

Serial output for JTAG boundary scan, ISP, and UJTAG usage.

TMS Test Mode Select

The TMS pin controls the use of the IEEE 1532 boundary scan pins (TCK, TDI, TDO, TRST). There is an internal weak pull-up resistor on the TMS pin.

TRST Boundary Scan Reset Pin

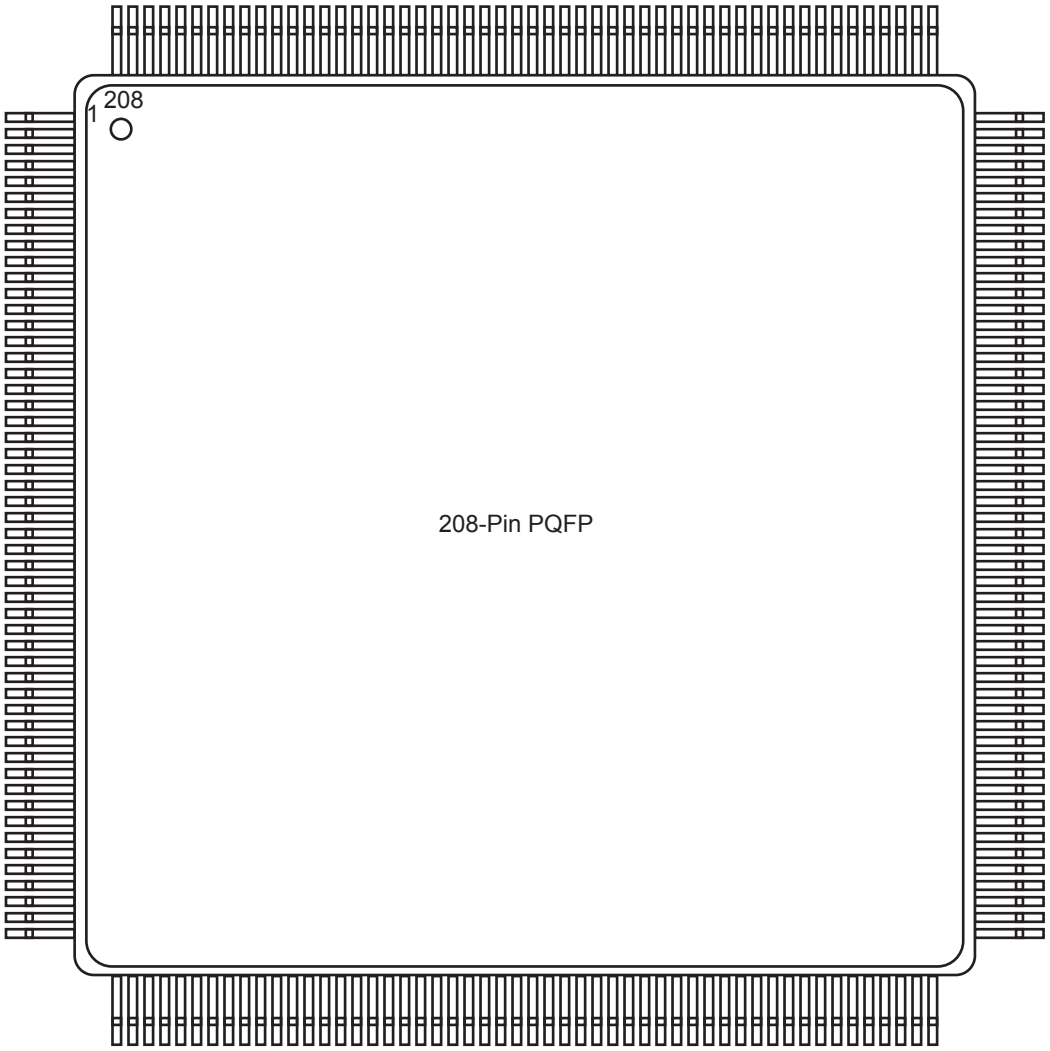
The TRST pin functions as an active-low input to asynchronously initialize (or reset) the boundary scan circuitry. There is an internal weak pull-up resistor on the TRST pin. If JTAG is not used, an external pull-down resistor could be included to ensure the test access port (TAP) is held in reset mode. The resistor values must be chosen from Table 3-1 and must satisfy the parallel resistance value requirement. The values in Table 3-1 correspond to the resistor recommended when a single device is used, and the equivalent parallel resistor when multiple devices are connected via a JTAG chain.

In critical applications, an upset in the JTAG circuit could allow entrance to an undesired JTAG state. In such cases, Microsemi recommends tying off TRST to GND through a resistor placed close to the FPGA pin.

Note that to operate at all VJTAG voltages, 500 Ω to 1 kΩ will satisfy the requirements.

4 – Package Pin Assignments

PQ208



Note: This is the top view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at *http://www.microsemi.com/products/fpga-soc/solutions*.

FG484	
Pin Number	A3PE3000 Function
A1	GND
A2	GND
A3	VCCIB0
A4	IO10NDB0V1
A5	IO10PDB0V1
A6	IO16NDB0V1
A7	IO16PDB0V1
A8	IO18PDB0V2
A9	IO24PDB0V2
A10	IO28NDB0V3
A11	IO28PDB0V3
A12	IO46PDB1V0
A13	IO54PDB1V1
A14	IO56NDB1V1
A15	IO56PDB1V1
A16	IO64NDB1V2
A17	IO64PDB1V2
A18	IO72NDB1V3
A19	IO74NDB1V4
A20	VCCIB1
A21	GND
A22	GND
AA1	GND
AA2	VCCIB6
AA3	IO228PDB5V4
AA4	IO224PDB5V3
AA5	IO218NDB5V3
AA6	IO218PDB5V3
AA7	IO212NDB5V2
AA8	IO212PDB5V2
AA9	IO198PDB5V0
AA10	IO198NDB5V0
AA11	IO188PPB4V4
AA12	IO180NDB4V3
AA13	IO180PDB4V3
AA14	IO170NDB4V2

FG484	
Pin Number	A3PE3000 Function
AA15	IO170PDB4V2
AA16	IO166NDB4V1
AA17	IO166PDB4V1
AA18	IO160NDB4V0
AA19	IO160PDB4V0
AA20	IO158NPB4V0
AA21	VCCIB3
AA22	GND
AB1	GND
AB2	GND
AB3	VCCIB5
AB4	IO216NDB5V2
AB5	IO216PDB5V2
AB6	IO210NDB5V2
AB7	IO210PDB5V2
AB8	IO208NDB5V1
AB9	IO208PDB5V1
AB10	IO197NDB5V0
AB11	IO197PDB5V0
AB12	IO174NDB4V2
AB13	IO174PDB4V2
AB14	IO172NDB4V2
AB15	IO172PDB4V2
AB16	IO168NDB4V1
AB17	IO168PDB4V1
AB18	IO162NDB4V1
AB19	IO162PDB4V1
AB20	VCCIB4
AB21	GND
AB22	GND
B1	GND
B2	VCCIB7
B3	IO06PPB0V0
B4	IO08NDB0V0
B5	IO08PDB0V0
B6	IO14NDB0V1

FG484	
Pin Number	A3PE3000 Function
B7	IO14PDB0V1
B8	IO18NDB0V2
B9	IO24NDB0V2
B10	IO34PDB0V4
B11	IO40PDB0V4
B12	IO46NDB1V0
B13	IO54NDB1V1
B14	IO62NDB1V2
B15	IO62PDB1V2
B16	IO68NDB1V3
B17	IO68PDB1V3
B18	IO72PDB1V3
B19	IO74PDB1V4
B20	IO76NPB1V4
B21	VCCIB2
B22	GND
C1	VCCIB7
C2	IO303PDB7V3
C3	IO305PDB7V3
C4	IO06NPB0V0
C5	GND
C6	IO12NDB0V1
C7	IO12PDB0V1
C8	VCC
C9	VCC
C10	IO34NDB0V4
C11	IO40NDB0V4
C12	IO48NDB1V0
C13	IO48PDB1V0
C14	VCC
C15	VCC
C16	IO70NDB1V3
C17	IO70PDB1V3
C18	GND
C19	IO76PPB1V4
C20	IO88NDB2V0

FG484	
Pin Number	A3PE3000 Function
N17	IO132NPB3V2
N18	IO117NPB3V0
N19	IO132PPB3V2
N20	GNDQ
N21	IO126NDB3V1
N22	IO128PDB3V1
P1	IO247PDB6V1
P2	IO253PDB6V2
P3	IO270NPB6V4
P4	IO261NPB6V3
P5	IO249PPB6V1
P6	IO259PDB6V3
P7	IO259NDB6V3
P8	VCCIB6
P9	GND
P10	VCC
P11	VCC
P12	VCC
P13	VCC
P14	GND
P15	VCCIB3
P16	GDB0/IO152NPB3V4
P17	IO136NDB3V2
P18	IO136PDB3V2
P19	IO138PDB3V3
P20	VMV3
P21	IO130PDB3V2
P22	IO128NDB3V1
R1	IO247NDB6V1
R2	IO245PDB6V1
R3	VCC
R4	IO249NPB6V1
R5	IO251NDB6V2
R6	IO251PDB6V2
R7	GEC0/IO236NPB6V0
R8	VMV5

FG484	
Pin Number	A3PE3000 Function
R9	VCCIB5
R10	VCCIB5
R11	IO196NDB5V0
R12	IO196PDB5V0
R13	VCCIB4
R14	VCCIB4
R15	VMV3
R16	VCCPLD
R17	GDB1/IO152PPB3V4
R18	GDC1/IO151PDB3V4
R19	IO138NDB3V3
R20	VCC
R21	IO130NDB3V2
R22	IO134PDB3V2
T1	IO243PPB6V1
T2	IO245NDB6V1
T3	IO243NPB6V1
T4	IO241PDB6V0
T5	IO241NDB6V0
T6	GEC1/IO236PPB6V0
T7	VCOMPLE
T8	GNDQ
T9	GEA2/IO233PPB5V4
T10	IO206NDB5V1
T11	IO202NDB5V1
T12	IO194NDB5V0
T13	IO186NDB4V4
T14	IO186PDB4V4
T15	GNDQ
T16	VCOMPLD
T17	VJTAG
T18	GDC0/IO151NDB3V4
T19	GDA1/IO153PDB3V4
T20	IO144PDB3V3
T21	IO140PDB3V3
T22	IO134NDB3V2

FG484	
Pin Number	A3PE3000 Function
U1	IO240PPB6V0
U2	IO238PDB6V0
U3	IO238NDB6V0
U4	GEB1/IO235PDB6V0
U5	GEB0/IO235NDB6V0
U6	VMV6
U7	VCCPLE
U8	IO233NPB5V4
U9	IO222PPB5V3
U10	IO206PDB5V1
U11	IO202PDB5V1
U12	IO194PDB5V0
U13	IO176NDB4V2
U14	IO176PDB4V2
U15	VMV4
U16	TCK
U17	VPUMP
U18	TRST
U19	GDA0/IO153NDB3V4
U20	IO144NDB3V3
U21	IO140NDB3V3
U22	IO142PDB3V3
V1	IO239PDB6V0
V2	IO240NPB6V0
V3	GND
V4	GEA1/IO234PDB6V0
V5	GEA0/IO234NDB6V0
V6	GNDQ
V7	GEC2/IO231PDB5V4
V8	IO222NPB5V3
V9	IO204NDB5V1
V10	IO204PDB5V1
V11	IO195NDB5V0
V12	IO195PDB5V0
V13	IO178NDB4V3
V14	IO178PDB4V3

FG896	
Pin Number	A3PE3000 Function
T11	VCC
T12	GND
T13	GND
T14	GND
T15	GND
T16	GND
T17	GND
T18	GND
T19	GND
T20	VCC
T21	VCCIB3
T22	IO109NPB2V3
T23	IO116NDB3V0
T24	IO118NDB3V0
T25	IO122NPB3V1
T26	GCA1/IO114PPB3V0
T27	GCB0/IO113NPB2V3
T28	GCA2/IO115PPB3V0
T29	VCCPLC
T30	IO121PDB3V0
U1	IO268PDB6V4
U2	IO264NDB6V3
U3	IO264PDB6V3
U4	IO258PDB6V3
U5	IO258NDB6V3
U6	IO257PPB6V2
U7	IO261PPB6V3
U8	IO265NDB6V3
U9	IO263NDB6V3
U10	VCCIB6
U11	VCC
U12	GND
U13	GND
U14	GND
U15	GND
U16	GND

FG896	
Pin Number	A3PE3000 Function
U17	GND
U18	GND
U19	GND
U20	VCC
U21	VCCIB3
U22	IO120PDB3V0
U23	IO128PDB3V1
U24	IO124PDB3V1
U25	IO124NDB3V1
U26	IO126PDB3V1
U27	IO129PDB3V1
U28	IO127PDB3V1
U29	IO125PDB3V1
U30	IO121NDB3V0
V1	IO268NDB6V4
V2	IO262PDB6V3
V3	IO260PDB6V3
V4	IO252PDB6V2
V5	IO257NPB6V2
V6	IO261NPB6V3
V7	IO255PDB6V2
V8	IO259PDB6V3
V9	IO259NDB6V3
V10	VCCIB6
V11	VCC
V12	GND
V13	GND
V14	GND
V15	GND
V16	GND
V17	GND
V18	GND
V19	GND
V20	VCC
V21	VCCIB3
V22	IO120NDB3V0

FG896	
Pin Number	A3PE3000 Function
V23	IO128NDB3V1
V24	IO132PDB3V2
V25	IO130PPB3V2
V26	IO126NDB3V1
V27	IO129NDB3V1
V28	IO127NDB3V1
V29	IO125NDB3V1
V30	IO123PDB3V1
W1	IO266NDB6V4
W2	IO262NDB6V3
W3	IO260NDB6V3
W4	IO252NDB6V2
W5	IO251NDB6V2
W6	IO251PDB6V2
W7	IO255NDB6V2
W8	IO249PPB6V1
W9	IO253PDB6V2
W10	VCCIB6
W11	VCC
W12	GND
W13	GND
W14	GND
W15	GND
W16	GND
W17	GND
W18	GND
W19	GND
W20	VCC
W21	VCCIB3
W22	IO134PDB3V2
W23	IO138PDB3V3
W24	IO132NDB3V2
W25	IO136NPB3V2
W26	IO130NPB3V2
W27	IO141PDB3V3
W28	IO135PDB3V2

Revision	Changes	Page
Advance v0.3 (continued)	The "Methodology" section was updated.	3-9
	The A3PE3000 "208-Pin PQFP" pin table was updated.	4-6

Microsemi Corporate Headquarters
One Enterprise, Aliso Viejo,
CA 92656 USA

Within the USA: +1 (800) 713-4113
Outside the USA: +1 (949) 380-6100
Sales: +1 (949) 380-6136
Fax: +1 (949) 215-4996

E-mail: sales.support@microsemi.com

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